

RF Power Field Effect Transistors

N-Channel Enhancement-Mode Lateral MOSFETs

Designed for N-CDMA base station applications with frequencies from 869 to 960 MHz. Suitable for multicarrier amplifier applications.

- Typical Single-Carrier N-CDMA Performance @ 880 MHz: $V_{DD} = 28$ Volts, $I_{DQ} = 1500$ mA, $P_{out} = 33$ Watts Avg., IS-95 CDMA (Pilot, Sync, Paging, Traffic Codes 8 Through 13). Channel Bandwidth = 1.2288 MHz. PAR = 9.8 dB @ 0.01% Probability on CCDF.
Power Gain — 19.7 dB
Drain Efficiency — 28.4%
ACPR @ 750 kHz Offset — -46.8 dBc in 30 kHz Bandwidth
- Capable of Handling 10:1 VSWR, @ 28 Vdc, 880 MHz, 150 Watts CW Output Power

Features

- Characterized with Series Equivalent Large-Signal Impedance Parameters
- Internally Matched for Ease of Use
- Qualified Up to a Maximum of 32 V_{DD} Operation
- Integrated ESD Protection
- Lower Thermal Resistance Package
- Low Gold Plating Thickness on Leads, 40 μ m Nominal.
- RoHS Compliant
- In Tape and Reel. R3 Suffix = 250 Units per 56 mm, 13 inch Reel.

MRF5S9150HR3
MRF5S9150HSR3

880 MHz, 33 W AVG., 28 V
SINGLE N-CDMA
LATERAL N-CHANNEL
RF POWER MOSFETs

CASE 465-06, STYLE 1
NI-780
MRF5S9150HR3

CASE 465A-06, STYLE 1
NI-780S
MRF5S9150HSR3

Table 1. Maximum Ratings

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	-0.5, +68	Vdc
Gate-Source Voltage	V_{GS}	-0.5, +15	Vdc
Storage Temperature Range	T_{stg}	- 65 to +150	°C
Case Operating Temperature	T_C	150	°C
Operating Junction Temperature	T_J	200	°C

Table 2. Thermal Characteristics

Characteristic	Symbol	Value ⁽¹⁾	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$		°C/W
Case Temperature 80°C, 150 W CW		0.34	
Case Temperature 76°C, 33 W CW		0.34	

Table 3. ESD Protection Characteristics

Test Methodology	Class
Human Body Model (per JESD22-A114)	1C (Minimum)
Machine Model (per EIA/JESD22-A115)	A (Minimum)
Charge Device Model (per JESD22-C101)	III (Minimum)

1. Refer to AN1955, *Thermal Measurement Methodology of RF Power Amplifiers*. Go to <http://www.freescale.com/rf>. Select Documentation/Application Notes - AN1955.

Table 4. Electrical Characteristics ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
Off Characteristics					
Zero Gate Voltage Drain Leakage Current ($V_{DS} = 68\text{ Vdc}$, $V_{GS} = 0\text{ Vdc}$)	I_{DSS}	—	—	10	μAdc
Zero Gate Voltage Drain Leakage Current ($V_{DS} = 28\text{ Vdc}$, $V_{GS} = 0\text{ Vdc}$)	I_{DSS}	—	—	1	μAdc
Gate-Source Leakage Current ($V_{GS} = 5\text{ Vdc}$, $V_{DS} = 0\text{ Vdc}$)	I_{GSS}	—	—	500	nAdc
On Characteristics					
Gate Threshold Voltage ($V_{DS} = 10\text{ Vdc}$, $I_D = 600\text{ }\mu\text{Adc}$)	$V_{GS(th)}$	2	3	4	Vdc
Gate Quiescent Voltage ($V_{DS} = 28\text{ Vdc}$, $I_D = 1500\text{ mAdc}$, Measured in Functional Test)	$V_{GS(Q)}$	3	4	5	Vdc
Drain-Source On-Voltage ($V_{GS} = 10\text{ Vdc}$, $I_D = 3.15\text{ Adc}$)	$V_{DS(on)}$	0.1	0.2	0.3	Vdc
Dynamic Characteristics ⁽¹⁾					
Reverse Transfer Capacitance ($V_{DS} = 28\text{ Vdc} \pm 30\text{ mV(rms)ac}$ @ 1 MHz, $V_{GS} = 0\text{ Vdc}$)	C_{rss}	—	3.1	—	pF
Output Capacitance ($V_{DS} = 28\text{ Vdc} \pm 30\text{ mV(rms)ac}$ @ 1 MHz, $V_{GS} = 0\text{ Vdc}$)	C_{oss}	—	91.5	—	pF
Functional Tests (In Freescale Test Fixture, 50 ohm system) $V_{DD} = 28\text{ Vdc}$, $I_{DQ} = 1500\text{ mA}$, $P_{out} = 33\text{ W Avg. N-CDMA}$, $f = 880\text{ MHz}$, Single-Carrier N-CDMA, 1.2288 MHz Channel Bandwidth Carrier. ACPR measured in 30 kHz Channel Bandwidth @ $\pm 750\text{ kHz}$ Offset. PAR = 9.8 dB @ 0.01% Probability on CCDF.					
Power Gain	G_{ps}	18.5	19.7	21.5	dB
Drain Efficiency	η_D	26.5	28.4	—	%
Adjacent Channel Power Ratio	ACPR	—	-46.8	-45	dBc
Input Return Loss	IRL	—	-20	-9	dB

1. Part internally input matched.

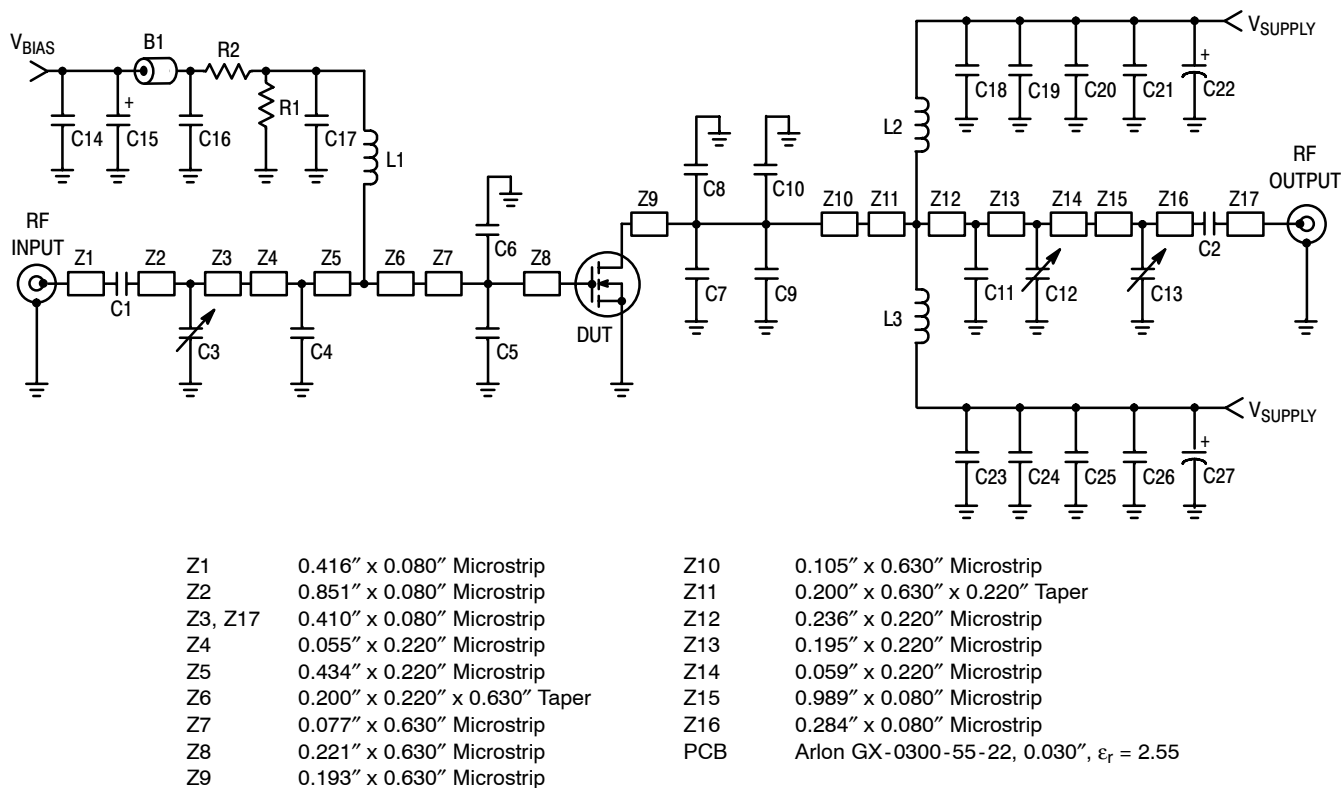


Figure 1. MRF5S9150HR3(HSR3) Test Circuit Schematic

Table 5. MRF5S9150HR3(HSR3) Test Circuit Component Designations and Values

Part	Description	Part Number	Manufacturer
B1	Small Ferrite Bead	2743019447	Fair Rite
C1, C2, C17	47 pF Chip Capacitors	100B470JP500X	ATC
C3, C12	0.8-8.0 pF Variable Capacitors, Gigatrim	27291SL	Johanson
C4	13 pF Chip Capacitor	100B130JP500X	ATC
C5, C6	15 pF Chip Capacitors	100B150JP500X	ATC
C7, C8	12 pF Chip Capacitors	100B120JP500X	ATC
C9, C10	4.3 pF Chip Capacitors	100B4R3JP500X	ATC
C11	8.2 pF Chip Capacitor	100B8R2JP500X	ATC
C13	0.6-4.5 pF Variable Capacitor, Gigatrim	27271SL	Johanson
C14	22 pF Chip Capacitor	100B220JP500X	ATC
C15	1 μ F, 50 V Tantalum Capacitor	T491C105K0J0AS	Kemit
C16	20K pF Chip Capacitor	CDR353P203AK0S	Kemit
C18, C23	180 pF Chip Capacitors	100B181JP500X	ATC
C19, C20, C21, C24, C25, C26	10 μ F, 50 V Chip Capacitors (2220)	GRM55DR61H106KA88B	Murata
C22, C27	470 μ F, 63 V Electrolytic Capacitors	KME63VB471M12x25LL	United Chemi-Con
L1, L2, L3	12.5 nH Inductors	A04T	Coilcraft
R1	180 k Ω , 1/4 W Chip Resistor		
R2	10 Ω , 1/4 W Chip Resistor		

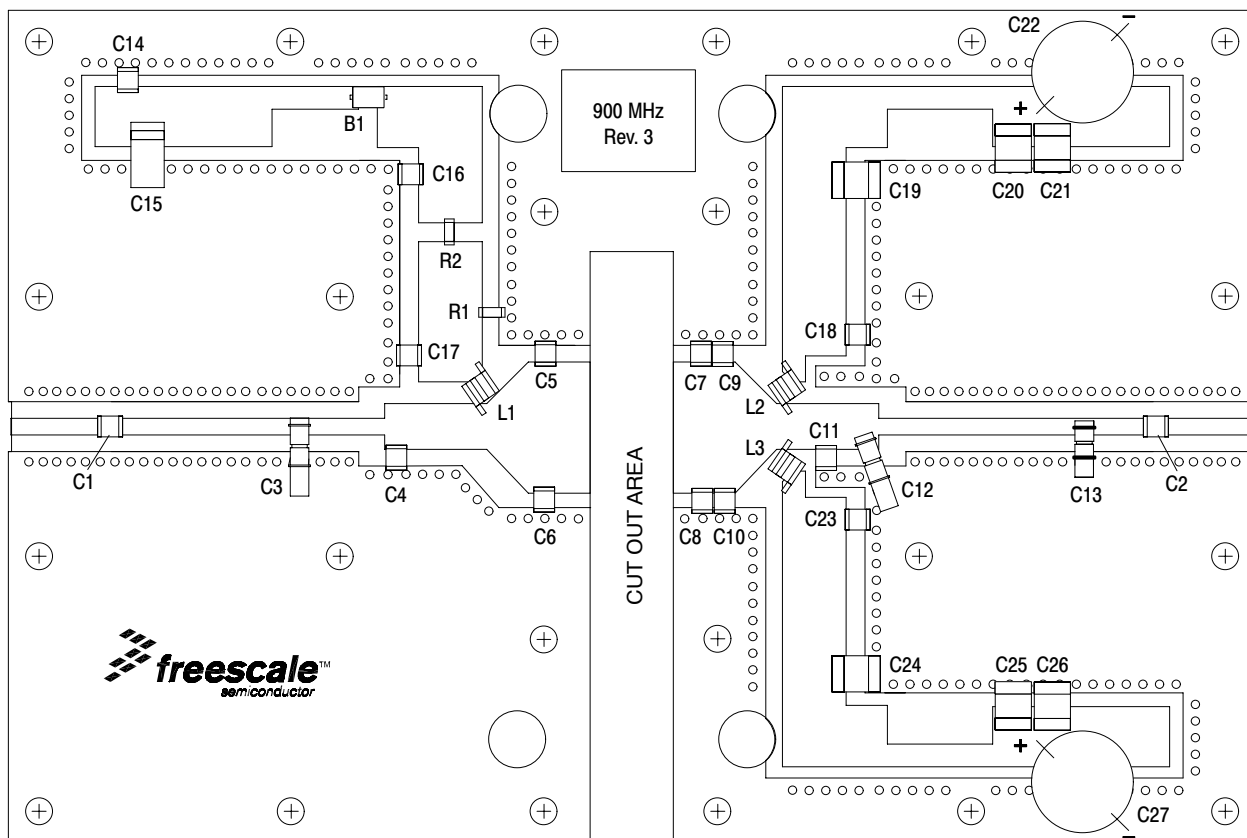


Figure 2. MRF5S9150HR3(HSR3) Test Circuit Component Layout

TYPICAL CHARACTERISTICS

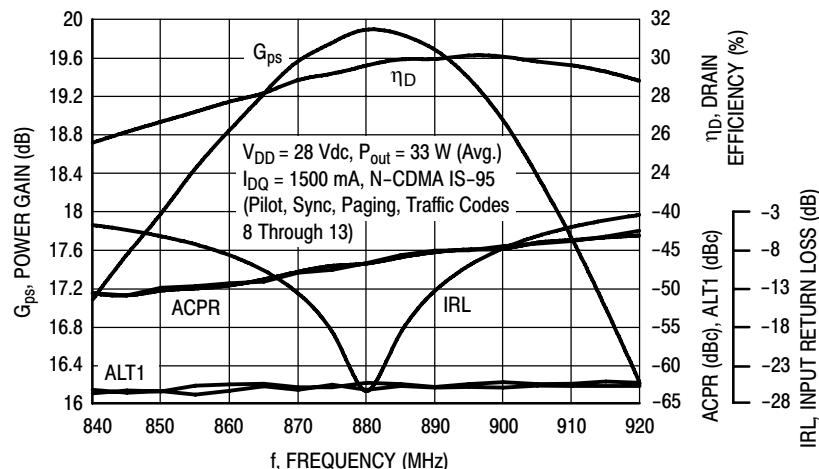


Figure 3. Single-Carrier N-CDMA Broadband Performance
@ $P_{out} = 33$ Watts Avg.

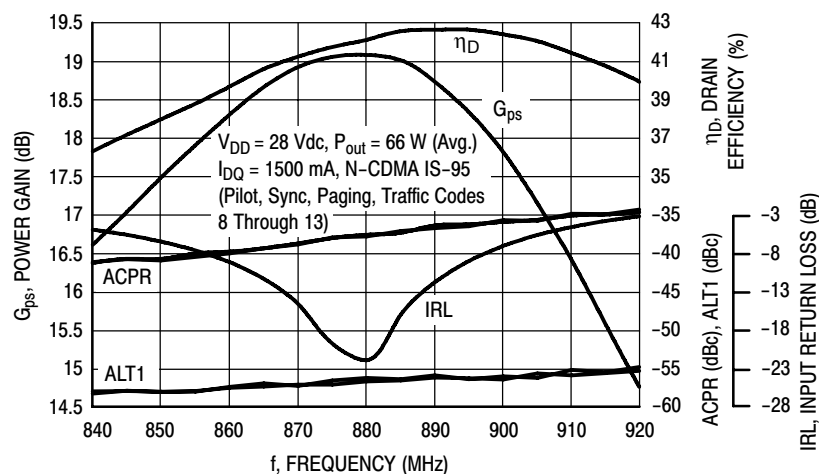


Figure 4. Single-Carrier N-CDMA Broadband Performance
@ $P_{out} = 66$ Watts Avg.

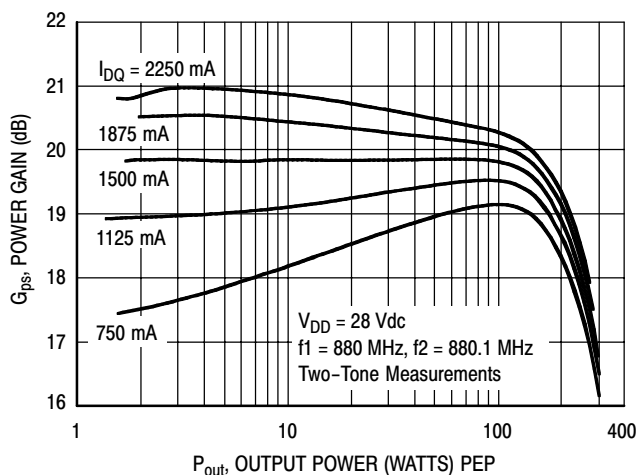


Figure 5. Two-Tone Power Gain versus
Output Power

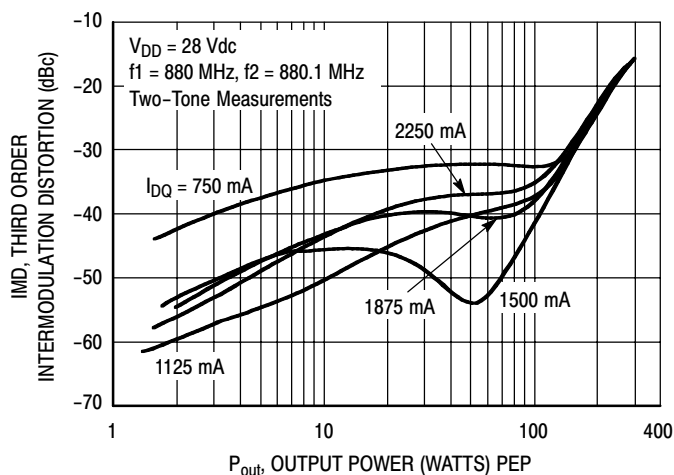


Figure 6. Third Order Intermodulation Distortion
versus Output Power

TYPICAL CHARACTERISTICS

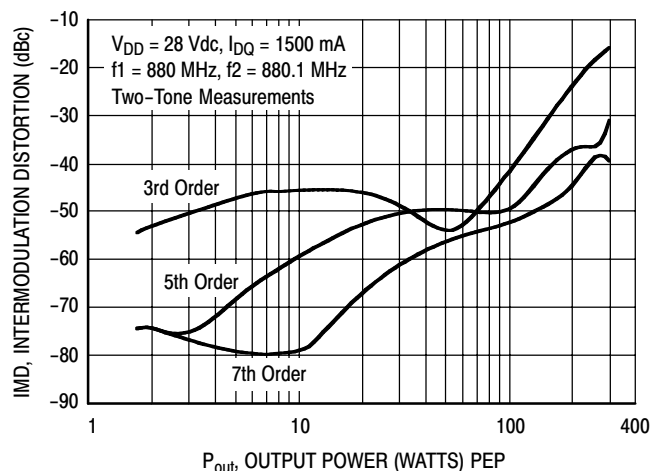


Figure 7. Intermodulation Distortion Products versus Output Power

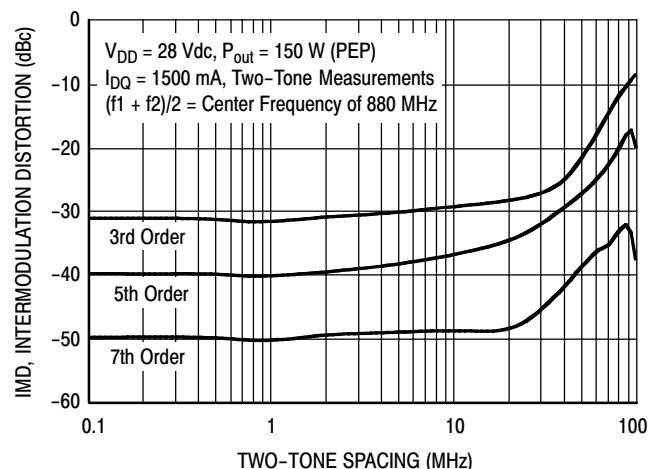


Figure 8. Intermodulation Distortion Products versus Tone Spacing

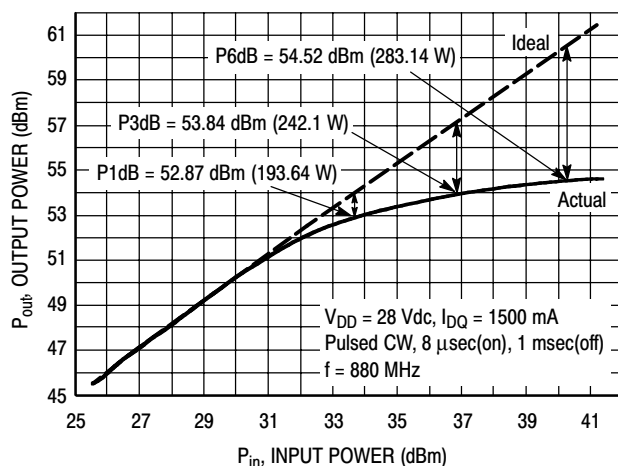


Figure 9. Pulse CW Output Power versus Input Power

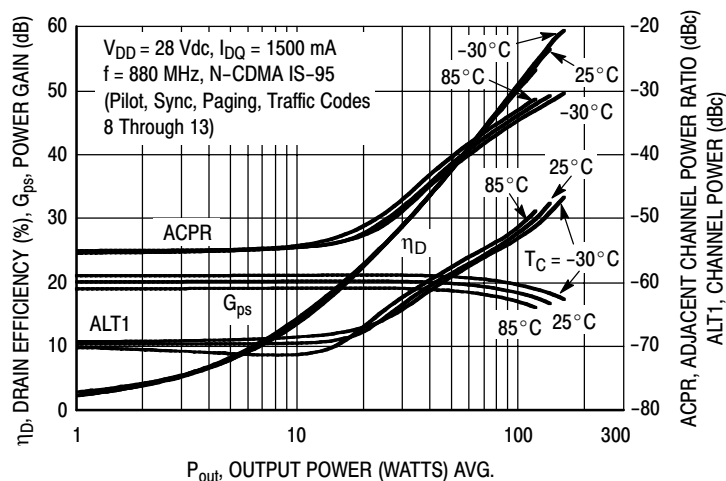


Figure 10. Single-Carrier N-CDMA ACPR, ALT1, Power Gain and Drain Efficiency versus Output Power

TYPICAL CHARACTERISTICS

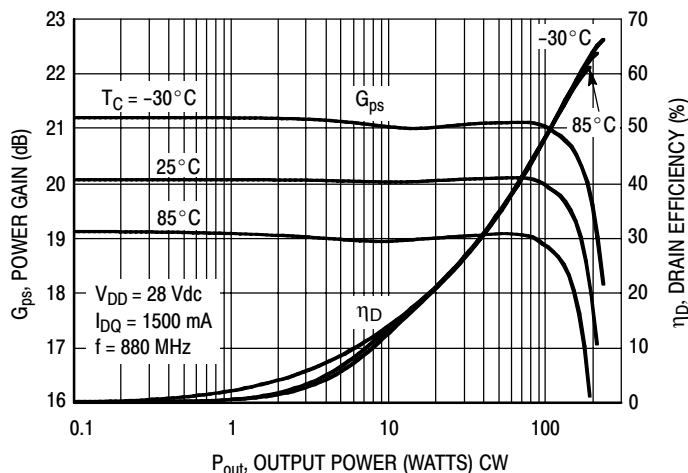


Figure 11. Power Gain and Drain Efficiency versus CW Output Power

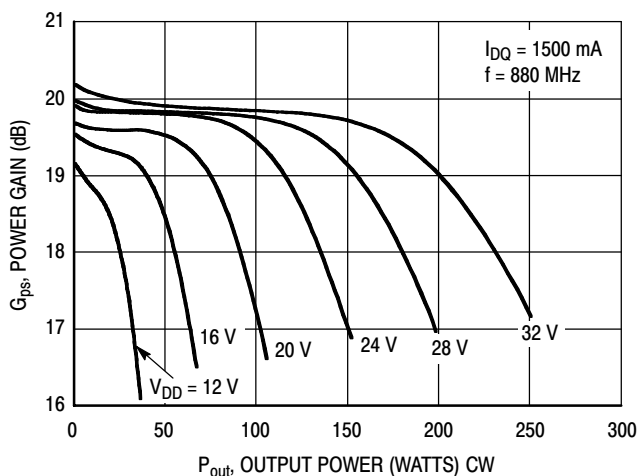
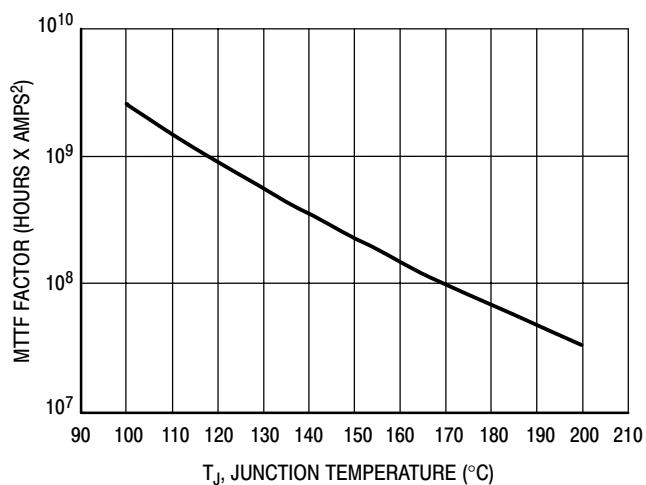


Figure 12. Power Gain versus Output Power



This above graph displays calculated MTTF in hours x ampere² drain current. Life tests at elevated temperatures have correlated to better than $\pm 10\%$ of the theoretical prediction for metal failure. Divide MTTF factor by I_D^2 for MTTF in a particular application.

Figure 13. MTTF Factor versus Junction Temperature

N-CDMA TEST SIGNAL

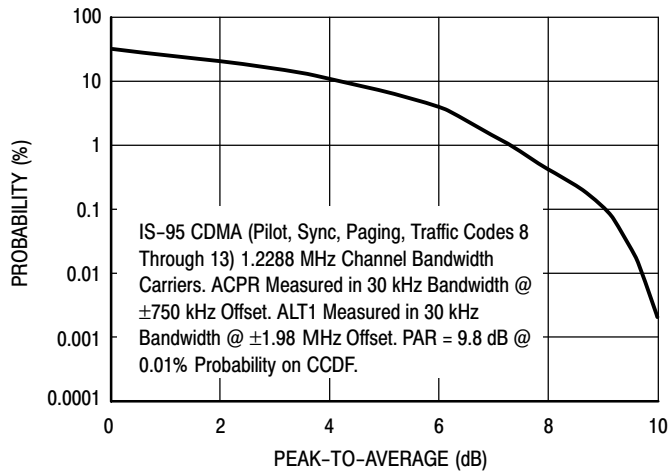


Figure 14. Single-Carrier CCDF N-CDMA

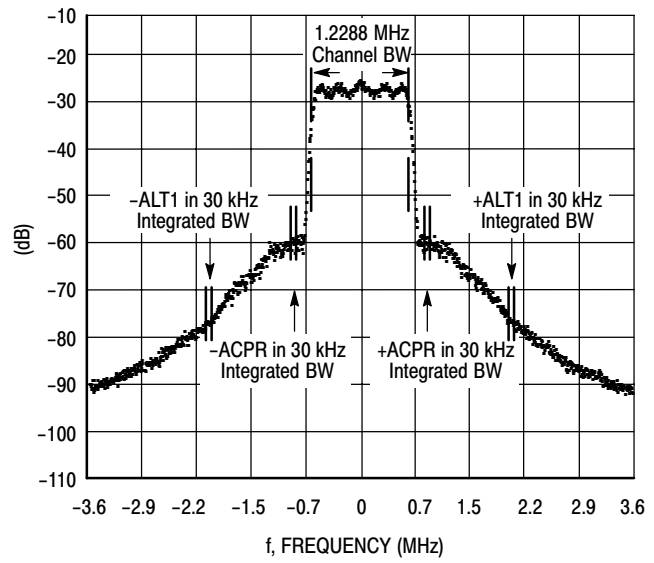
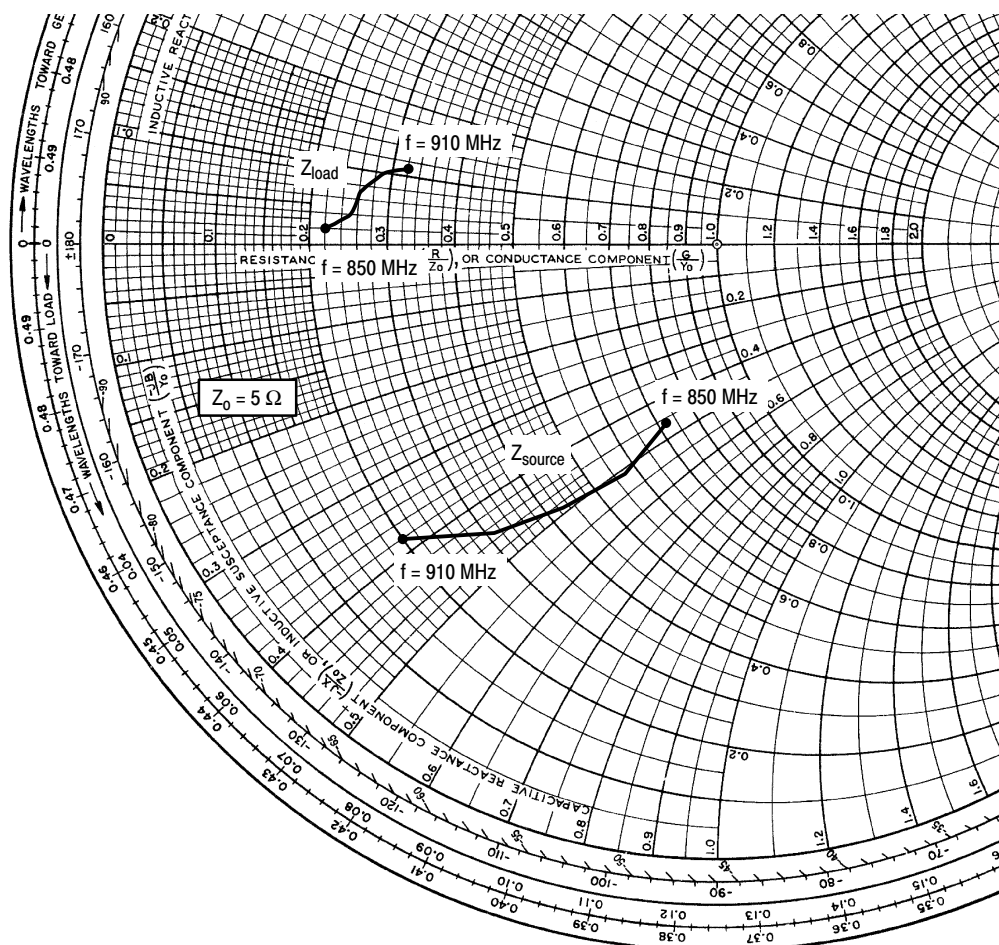


Figure 15. Single-Carrier N-CDMA Spectrum



$V_{DD} = 28 \text{ Vdc}$, $I_{DQ} = 1500 \text{ mA}$, $P_{out} = 33 \text{ W Avg.}$

f MHz	Z_{source} Ω	Z_{load} Ω
850	$3.61 - j2.30$	$1.12 + j0.09$
865	$2.85 - j2.54$	$1.24 + j0.22$
880	$2.13 - j2.47$	$1.31 + j0.36$
895	$1.53 - j2.27$	$1.46 + j0.48$
910	$1.02 - j1.90$	$1.61 + j0.53$

Z_{source} = Test circuit impedance as measured from gate to ground.

Z_{load} = Test circuit impedance as measured from drain to ground.

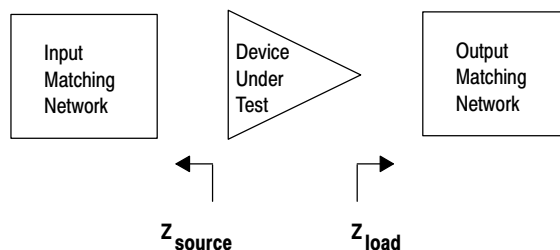


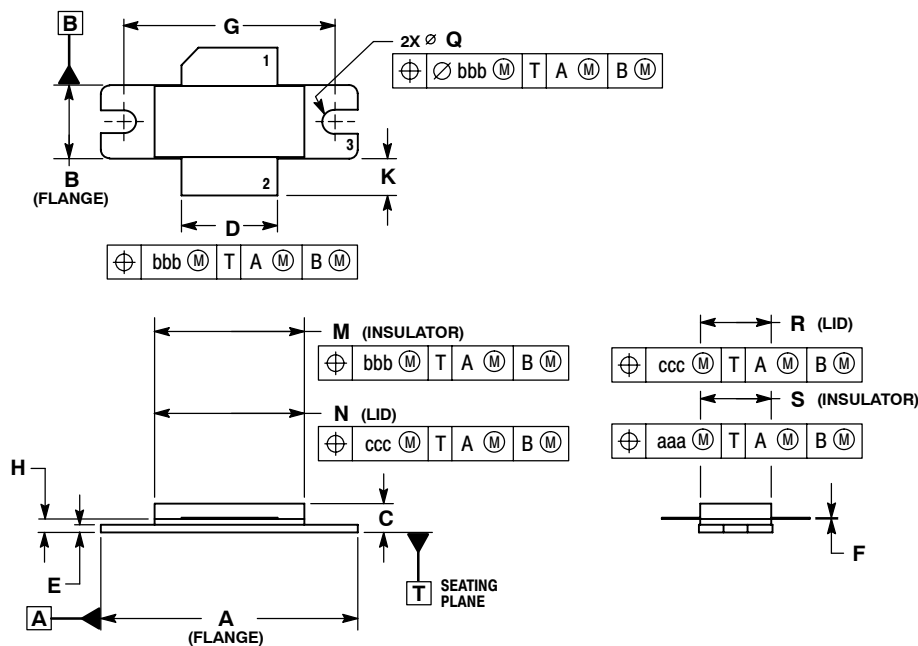
Figure 16. Series Equivalent Source and Load Impedance

NOTES

ARCHIVE INFORMATION

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PACKAGE DIMENSIONS



NOTES:

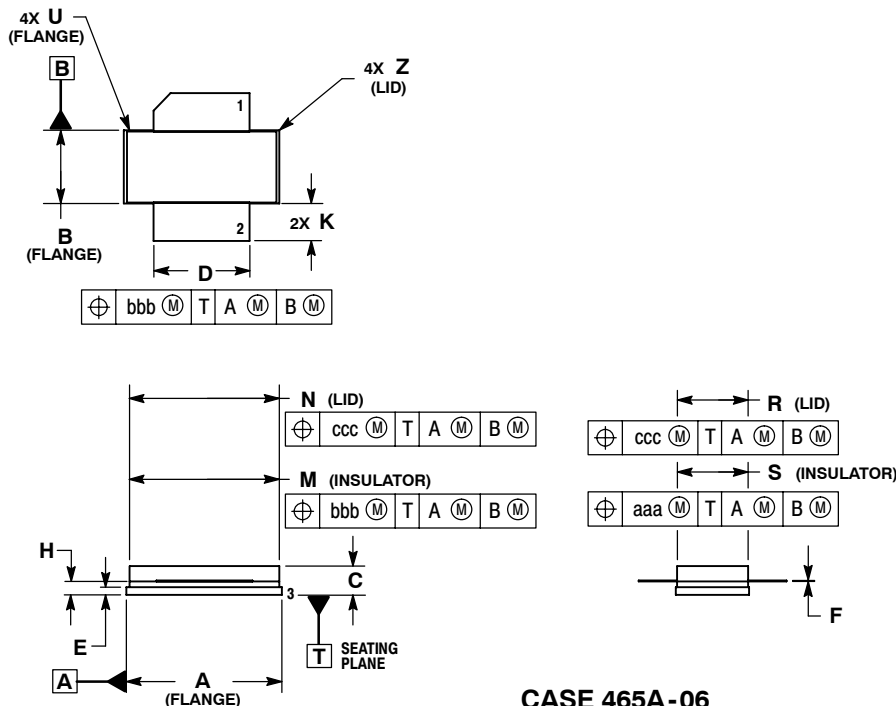
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2. CONTROLLING DIMENSION: INCH.
3. DELETED
4. DIMENSION H IS MEASURED 0.030 (0.762) AWAY FROM PACKAGE BODY.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	1.335	1.345	33.91	34.16
B	0.380	0.390	9.65	9.91
C	0.125	0.170	3.18	4.32
D	0.495	0.505	12.57	12.83
E	0.035	0.045	0.89	1.14
F	0.003	0.006	0.08	0.15
G	1.100 BSC		27.94 BSC	
H	0.057	0.067	1.45	1.70
K	0.170	0.210	4.32	5.33
M	0.774	0.786	19.66	19.96
N	0.772	0.788	19.60	20.00
Q	Ø 118	Ø 138	Ø 3.00	Ø 3.51
R	0.365	0.375	9.27	9.53
S	0.365	0.375	9.27	9.52
aaa	0.005 REF		0.127 REF	
bbb	0.010 REF		0.254 REF	
ccc	0.015 REF		0.381 REF	

STYLE 1:

1. DRAIN
2. GATE
3. SOURCE

**CASE 465-06
ISSUE G
NI-780
MRF5S9150HR3**



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M-1994.
2. CONTROLLING DIMENSION: INCH.
3. DELETED
4. DIMENSION H IS MEASURED 0.030 (0.762) AWAY FROM PACKAGE BODY.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.805	0.815	20.45	20.70
B	0.380	0.390	9.65	9.91
C	0.125	0.170	3.18	4.32
D	0.495	0.505	12.57	12.83
E	0.035	0.045	0.89	1.14
F	0.003	0.006	0.08	0.15
H	0.057	0.067	1.45	1.70
K	0.170	0.210	4.32	5.33
M	0.774	0.786	19.61	20.02
N	0.772	0.788	19.61	20.02
R	0.365	0.375	9.27	9.53
S	0.365	0.375	9.27	9.52
U	---	0.040	---	1.02
Z	---	0.030	---	0.76
aaa	0.005 REF		0.127 REF	
bbb	0.010 REF		0.254 REF	
ccc	0.015 REF		0.381 REF	

STYLE 1:

1. DRAIN
2. GATE
5. SOURCE

**CASE 465A-06
ISSUE H
NI-780S
MRF5S9150HSR3**

MRF5S9150HR3 MRF5S9150HSR3

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Freescale Semiconductor
Technical Information Center, CH370
1300 N. Alma School Road
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+1-800-521-6274 or +1-480-768-2130
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Europe, Middle East, and Africa:
Freescale Halbleiter Deutschland GmbH
Technical Information Center
Schatzbogen 7
81829 Muenchen, Germany
+44 1296 380 456 (English)
+46 8 52200080 (English)
+49 89 92103 559 (German)
+33 1 69 35 48 48 (French)
support@freescale.com

Japan:
Freescale Semiconductor Japan Ltd.
Headquarters
ARCO Tower 15F
1-8-1, Shimo-Meguro, Meguro-ku,
Tokyo 153-0064
Japan
0120 191014 or +81 3 5437 9125
support.japan@freescale.com

Asia/Pacific:
Freescale Semiconductor Hong Kong Ltd.
Technical Information Center
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+800 2666 8080
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